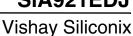
HALOGEN

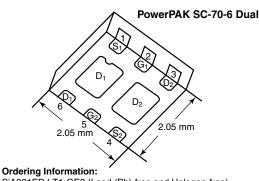
FREE





Dual P-Channel 20 V (D-S) MOSFET

PRODUCT SUMMARY									
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A)	Q _g (Typ.)						
- 20	$0.059 \text{ at V}_{GS} = -4.5 \text{ V}$	- 4.5 ^a	4.9 nC						
	0.098 at V _{GS} = - 2.5 V	- 4.5 ^a	4.9110						



SiA921EDJ-T1-GE3 (Lead (Pb)-free and Halogen-free) SiA921EDJ-T4-GE3 (Lead (Pb)-free and Halogen-free)

Marking Code Part # code ot Traceability and Date code

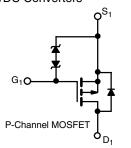
FEATURES

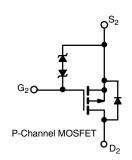
- TrenchFET® Power MOSFET
- Thermally Enhanced PowerPAK® SC-70 Package
 - Small Footprint Area
 - Low On-Resistance
- Typical ESD Protection: 1700 V
- High Speed Switching
- Material categorization:

For definitions of compliance please see www.vishay.com/doc?99912

APPLICATIONS

- Load Switch, PA Switch and Battery Switch for Portable **Devices**
- DC/DC Converters





Parameter		Symbol	Limit	Unit		
Drain-Source Voltage		V _{DS}	- 20	V		
Gate-Source Voltage		V _{GS}	± 12	v		
Continuous Drain Current (T _J = 150 °C)	$T_{C} = 25 ^{\circ}\text{C}$ $T_{C} = 70 ^{\circ}\text{C}$ $T_{A} = 25 ^{\circ}\text{C}$ $T_{A} = 70 ^{\circ}\text{C}$	I _D	- 4.5 ^a - 4.5 ^a - 4.5 ^a - 4.5 ^a , b, c - 3.7 ^{b, c}	A		
Pulsed Drain Current	•	I _{DM}	- 15			
Continuous Source-Drain Diode Current	$T_C = 25 ^{\circ}\text{C}$ $T_A = 25 ^{\circ}\text{C}$	I _S	- 4.5 ^a - 1.6 ^{b, c}]		
Maximum Power Dissipation	$T_{C} = 25 ^{\circ}\text{C}$ $T_{C} = 70 ^{\circ}\text{C}$ $T_{A} = 25 ^{\circ}\text{C}$ $T_{A} = 70 ^{\circ}\text{C}$	P _D	7.8 5 1.9 ^{b, c} 1.2 ^{b, c}	w		
Operating Junction and Storage Temperature Ra	ange	T _J , T _{stg}	- 55 to 150	°C		
Soldering Recommendations (Peak Temperature	e) ^{d, e}		260	\neg		

THERMAL RESISTANCE RATINGS									
Parameter		Symbol	Typical	Maximum	Unit				
Maximum Junction-to-Ambient ^{b, f}	t ≤ 5 s	R _{thJA}	52	65	°C/W				
Maximum Junction-to-Case (Drain)	Steady State	R _{thJC}	12.5	16	O/ VV				

Notes:

- a. Package limited.
- b. Surface mounted on 1" x 1" FR4 board.
- d. See solder profile (www.vishay.com/doc?73257). The PowerPAK SC-70 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.
- f. Maximum under steady state conditions is 110 °C/W.

Document Number: 64734 S12-2731-Rev. C, 12-Nov-12 For technical questions, contact:: pmostechsupport@vishay.com

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SPECIFICATIONS (T _J = 25 °C, unless otherwise noted) Parameter Symbol Test Conditions Min. Typ. Max.								
Static	,							
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_{D} = -250 \mu\text{A}$	- 20			V		
V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_{J}$	J 050A		- 14		14/00		
V _{GS(th)} Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	I _D = - 250 μA		2.5		mV/°C		
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	- 0.5		- 1.4	V		
Oaks Oassas Lasksons		$V_{DS} = 0 \text{ V}, V_{GS} = \pm 4.5 \text{ V}$			± 1			
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 12 \text{ V}$			± 10	μΑ		
Zovo Coto Voltogo Dvoin Curvent	I _{DSS}	V _{DS} = - 20 V, V _{GS} = 0 V			- 1			
Zero Gate Voltage Drain Current		$V_{DS} = -20 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 ^{\circ}\text{C}$			- 10			
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \le -5 \text{ V}, V_{GS} = -4.5 \text{ V}$	- 15			Α		
	В	$V_{GS} = -4.5 \text{ V}, I_D = -3.6 \text{ A}$		0.048	0.059	Ω		
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 2.5 V, I _D = - 1.5 A		0.080	0.098			
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 10 V, I _D = - 3.6 A		11		S		
Dynamic ^b				•		•		
Total Cata Chause		V _{DS} = - 10 V, V _{GS} = - 10 V, I _D = - 4.7 A		15	23	nC		
Total Gate Charge	Q_g			7.1	11			
Gate-Source Charge	Q _{gs}	$V_{DS} = -10 \text{ V}, V_{GS} = -4.5 \text{ V}, I_{D} = -4.7 \text{ A}$		1.3				
Gate-Drain Charge	Q _{gd}			2.1				
Gate Resistance	Resistance R _g			6.3		Ω		
Turn-On Delay Time	t _{d(on)}			20	30	-		
Rise Time	t _r	$V_{DD} = -10 \text{ V}, R_{L} = 2.7 \Omega$		20	30			
Turn-Off Delay Time	t _{d(off)}	$I_D \cong$ - 3.7 A, V_{GEN} = - 4.5 V, R_g = 1 Ω		25	40			
Fall Time	t _f			10	15			
Turn-On Delay Time	t _{d(on)}			5	10	ns		
Rise Time	t _r	$V_{DD} = -10 \text{ V}, R_{L} = 2.7 \Omega$		12	20	- - -		
Turn-Off Delay Time	t _{d(off)}	$I_D \cong -3.7 \text{ A}, V_{GEN} = -10 \text{ V}, R_g = 1 \Omega$		25	40			
Fall Time	t _f			10	15			
Drain-Source Body Diode Characteristics								
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C			- 4.5	Α		
Pulse Diode Forward Current	I _{SM}				- 15			
Body Diode Voltage	V_{SD}	$I_S = -3.7 \text{ A}, V_{GS} = 0 \text{ V}$		- 0.9	- 1.2	V		
Body Diode Reverse Recovery Time	t _{rr}			15	30	ns		
Body Diode Reverse Recovery Charge	Q _{rr}	I _F = - 3.7 A, dl/dt = 100 A/μs, T _{.I} = 25 °C		6	12	nC		
Reverse Recovery Fall Time	t _a	$\frac{1}{1}$ $\frac{1}$		8.5		20		
Reverse Recovery Rise Time	t _b			6.5		ns		

Notes:

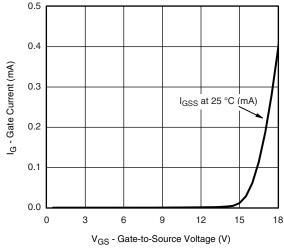
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

a. Pulse test; pulse width \leq 300 $\mu s,$ duty cycle \leq 2 %.

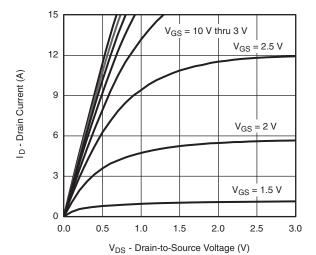
b. Guaranteed by design, not subject to production testing.



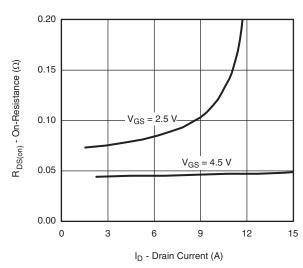
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



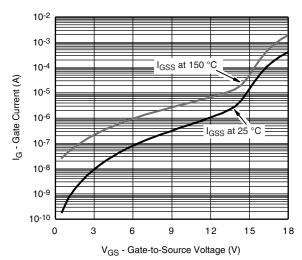
Gate Current vs. Gate-to-Source Voltage



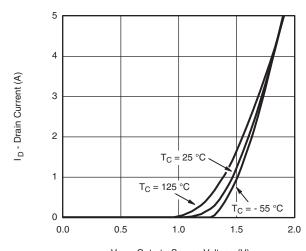
Output Characteristics



On-Resistance vs. Drain Current and Gate Voltage

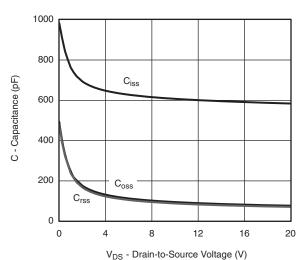


Gate Current vs. Gate-to-Source Voltage



V_{GS} - Gate-to-Source Voltage (V)

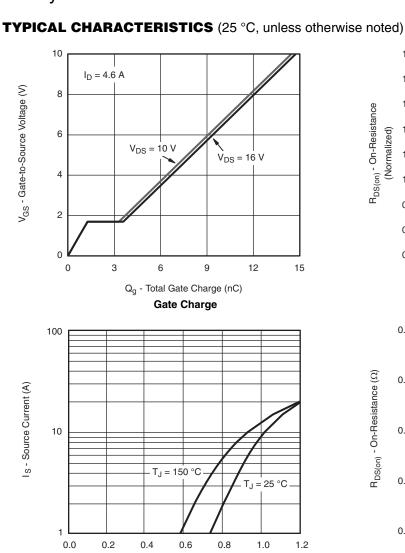




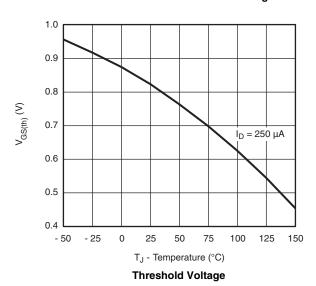
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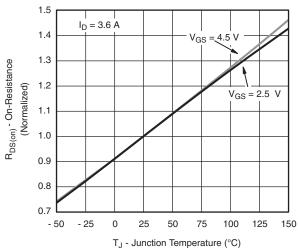
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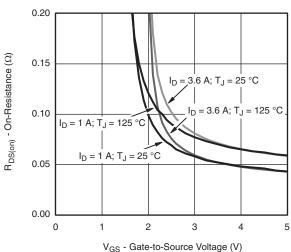


V_{SD} - Source-to-Drain Voltage (V) Source-Drain Diode Forward Voltage

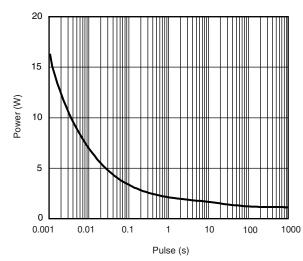




On-Resistance vs. Junction Temperature



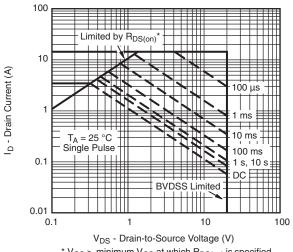
On-Resistance vs. Gate-to-Source Voltage



Single Pulse Power, Junction-to-Ambient



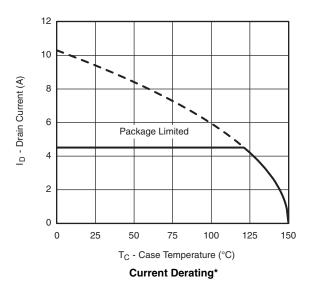
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

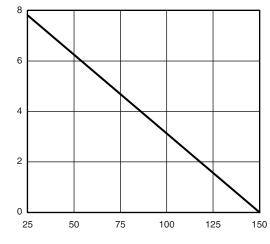


* V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area, Junction-to-Ambient

Power Dissipation (W)



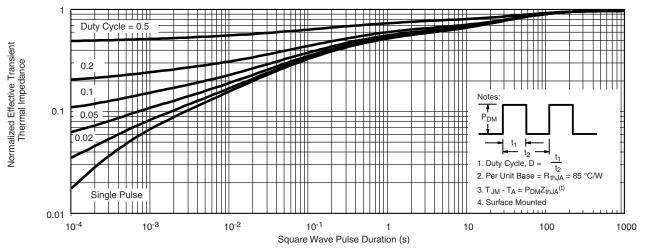


T_C - Case Temperature (°C)

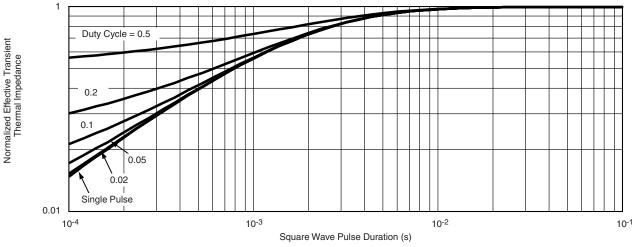
Power Derating

 $^{^{\}star}$ The power dissipation P_D is based on $T_{J(max.)}$ = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

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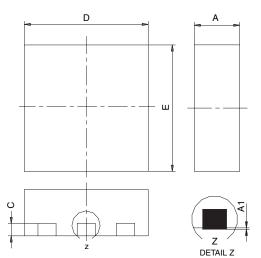
PowerPAK® SC70-6L





BACKSIDE VIEW OF SINGLE

BACKSIDE VIEW OF DUAL



- All dimensions are in millimeters
 Package outline exclusive of mold flash and metal burr
 Package outline inclusive of plating

	SINGLE PAD						DUAL PAD						
DIM	MILLIMETERS			INCHES			MILLIMETERS			INCHES			
	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max	
Α	0.675	0.75	0.80	0.027	0.030	0.032	0.675	0.75	0.80	0.027	0.030	0.032	
A1	0	-	0.05	0	-	0.002	0	-	0.05	0	-	0.002	
b	0.23	0.30	0.38	0.009	0.012	0.015	0.23	0.30	0.38	0.009	0.012	0.015	
С	0.15	0.20	0.25	0.006	0.008	0.010	0.15	0.20	0.25	0.006	0.008	0.010	
D	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085	
D1	0.85	0.95	1.05	0.033	0.037	0.041	0.513	0.613	0.713	0.020	0.024	0.028	
D2	0.135	0.235	0.335	0.005	0.009	0.013							
E	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085	
E1	1.40	1.50	1.60	0.055	0.059	0.063	0.85	0.95	1.05	0.033	0.037	0.041	
E2	0.345	0.395	0.445	0.014	0.016	0.018							
E3	0.425	0.475	0.525	0.017	0.019	0.021							
е		0.65 BSC			0.026 BSC			0.65 BSC			0.026 BSC		
K		0.275 TYP	1		0.011 TYP	1	0.275 TYP		0.011 TYP				
K1		0.400 TYP	1	0.016 TYP			0.320 TYP			0.013 TYP			
K2		0.240 TYP 0.009 TYP			0.252 TYP			0.010 TYP					
К3		0.225 TYP	1	0.009 TYP									
K4		0.355 TYP		0.014 TYP									
L	0.175	0.275	0.375	0.007	0.011	0.015	0.175	0.275	0.375	0.007	0.011	0.015	
Т							0.05	0.10	0.15	0.002	0.004	0.006	
FCN: C-07431 – Rev. C. 06-Aug-07													

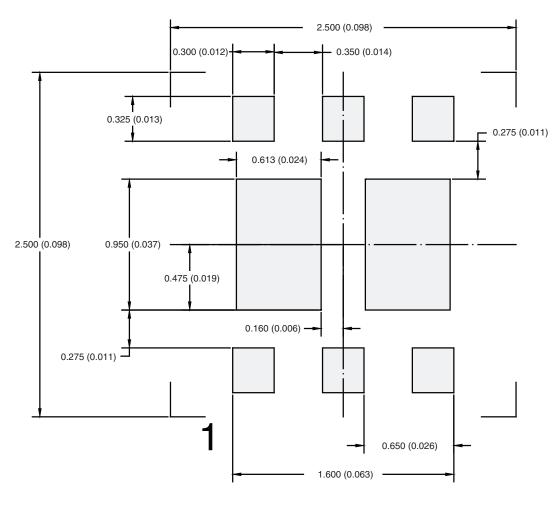
DWG: 5934

Document Number: 73001 06-Aug-07

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RECOMMENDED PAD LAYOUT FOR PowerPAK® SC70-6L Dual



Dimensions in mm (inches)

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